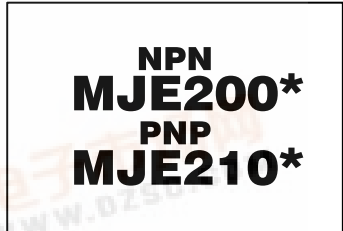


# Complementary Silicon Power Plastic Transistors

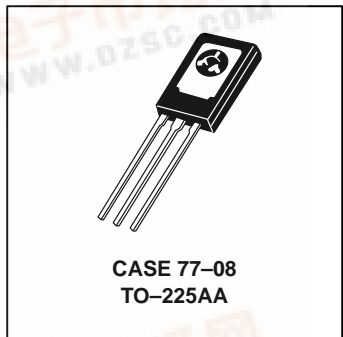
... designed for low voltage, low-power, high-gain audio amplifier applications.

- Collector-Emitter Sustaining Voltage —  
 $V_{CE(sus)} = 25 \text{ Vdc (Min) @ } I_C = 10 \text{ mA}$
- High DC Current Gain —  $h_{FE} = 70 \text{ (Min) @ } I_C = 500 \text{ mA}$   
 $= 45 \text{ (Min) @ } I_C = 2.0 \text{ Adc}$   
 $= 10 \text{ (Min) @ } I_C = 5.0 \text{ Adc}$
- Low Collector-Emitter Saturation Voltage —  
 $V_{CE(sat)} = 0.3 \text{ Vdc (Max) @ } I_C = 500 \text{ mA}$   
 $= 0.75 \text{ Vdc (Max) @ } I_C = 2.0 \text{ Adc}$
- High Current-Gain — Bandwidth Product —  
 $f_T = 65 \text{ MHz (Min) @ } I_C = 100 \text{ mA}$
- Annular Construction for Low Leakage —  
 $I_{CBO} = 100 \text{ nAdc @ Rated } V_{CB}$



\*Motorola Preferred Device

**5 AMPERE  
 POWER TRANSISTORS  
 COMPLEMENTARY  
 SILICON  
 25 VOLTS  
 15 WATTS**



## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{CB}$	40	Vdc
Collector-Emitter Voltage	$V_{CEO}$	25	Vdc
Emitter-Base Voltage	$V_{EB}$	8.0	Vdc
Collector Current — Continuous	$I_C$	5.0	Adc
Peak		10	
Base Current	$I_B$	1.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	$P_D$	15	Watts
Derate above $25^\circ\text{C}$		0.12	W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	1.5	Watts
Derate above $25^\circ\text{C}$		0.012	W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$\theta_{JC}$	8.34	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	$\theta_{JA}$	83.4	$^\circ\text{C/W}$

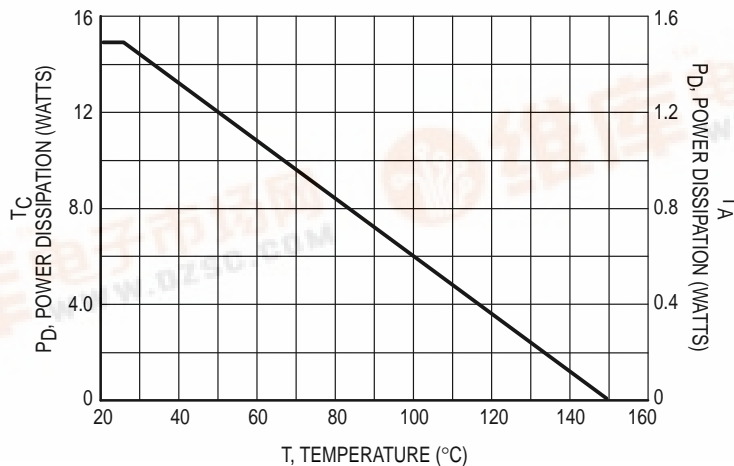


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 7



**MOTOROLA**

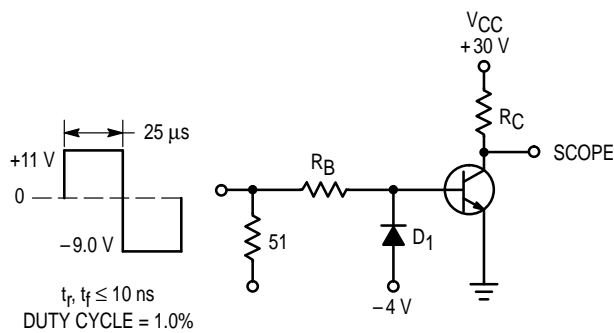
# MJE200 MJE210

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Sustaining Voltage (1) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	25	—	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 40 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = 40 Vdc, I <sub>E</sub> = 0, T <sub>J</sub> = 125°C)	I <sub>CBO</sub>	—	100	nAdc μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 8.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	—	100	nAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain (1) (I <sub>C</sub> = 500 mA, V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 2.0 Adc, V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 2.0 Vdc)	h <sub>FE</sub>	70 45 10	— 180 —	—
Collector–Emitter Saturation Voltage (1) (I <sub>C</sub> = 500 mA, I <sub>B</sub> = 50 mA) (I <sub>C</sub> = 2.0 Adc, I <sub>B</sub> = 200 mA) (I <sub>C</sub> = 5.0 Adc, I <sub>B</sub> = 1.0 Adc)	V <sub>CE(sat)</sub>	— — —	0.3 0.75 1.8	Vdc
Base–Emitter Saturation Voltage (1) (I <sub>C</sub> = 5.0 Adc, I <sub>B</sub> = 1.0 Adc)	V <sub>BE(sat)</sub>	—	2.5	Vdc
Base–Emitter On Voltage (1) (I <sub>C</sub> = 2.0 Adc, V <sub>CE</sub> = 1.0 Vdc)	V <sub>BE(on)</sub>	—	1.6	Vdc
<b>DYNAMIC CHARACTERISTICS</b>				
Current–Gain — Bandwidth Product (2) (I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 10 MHz)	f <sub>T</sub>	65	—	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz)	C <sub>ob</sub>	—	80	pF
	MJE200 MJE210	— —	120	

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≈ 2.0%.

(2) f<sub>T</sub> = |h<sub>fe</sub>| • f<sub>test</sub>.



R<sub>B</sub> and R<sub>C</sub> VARIED TO OBTAIN DESIRED CURRENT LEVELS  
 D<sub>1</sub> MUST BE FAST RECOVERY TYPE, e.g.:  
 1N5825 USED ABOVE I<sub>B</sub> ≈ 100 mA  
 MSD6100 USED BELOW I<sub>B</sub> ≈ 100 mA

Figure 2. Switching Time Test Circuit

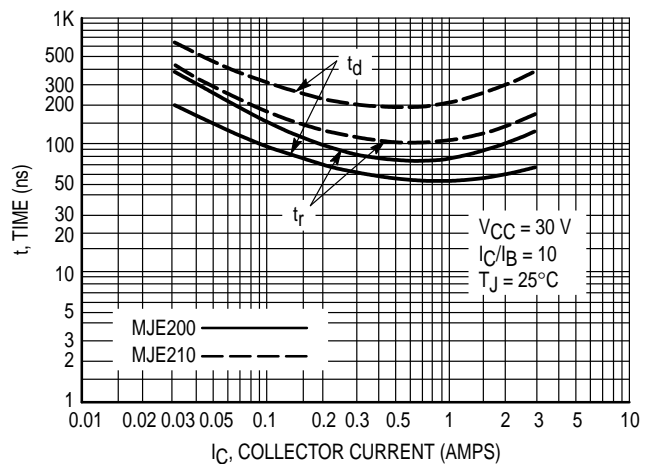


Figure 3. Turn–On Time

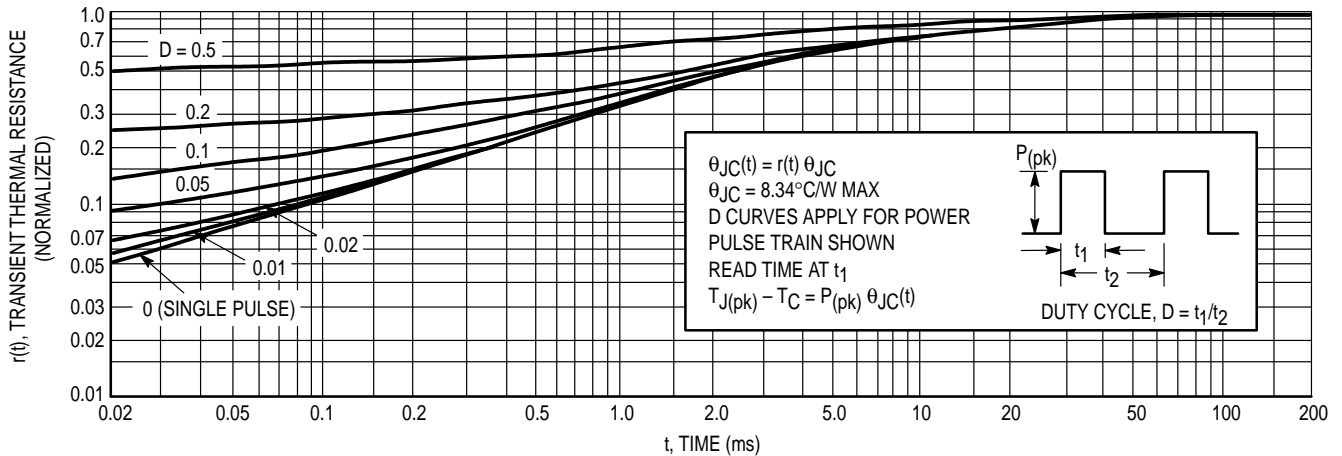


Figure 4. Thermal Response

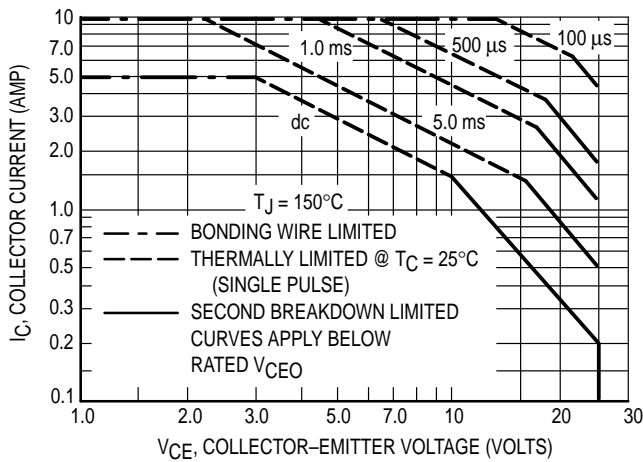


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

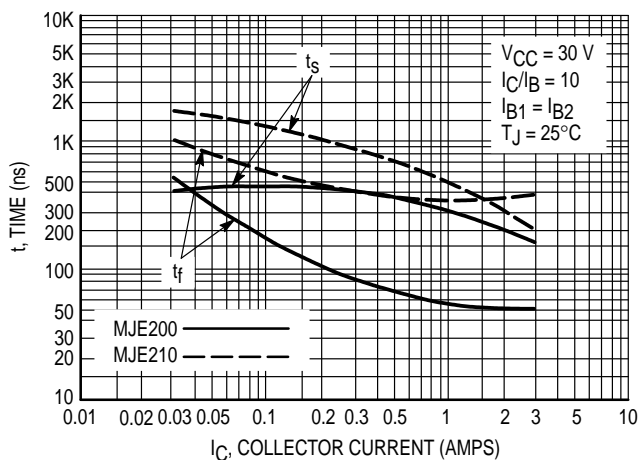


Figure 6. Turn-Off Time

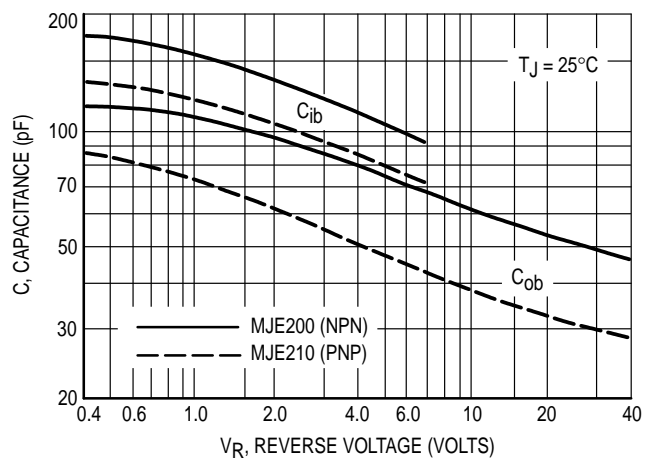
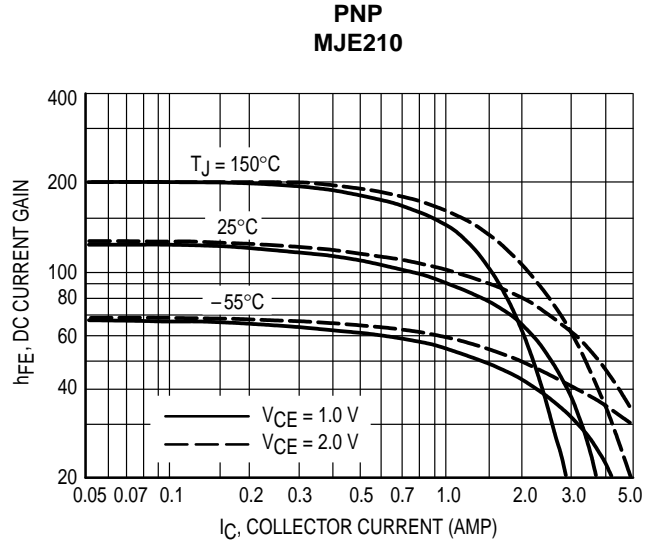
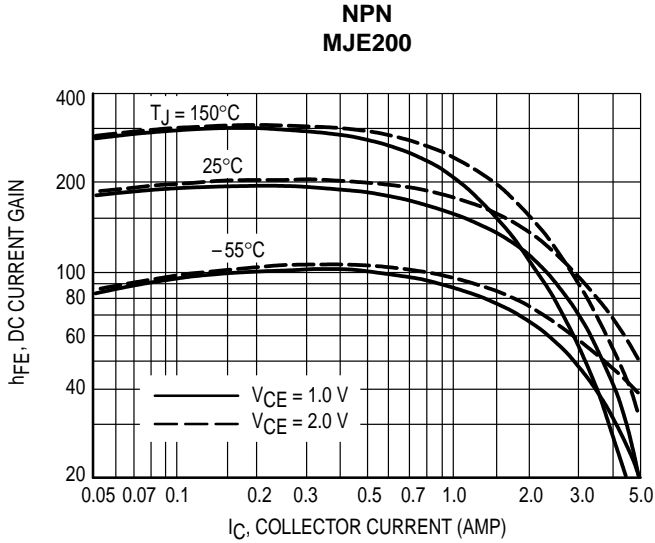
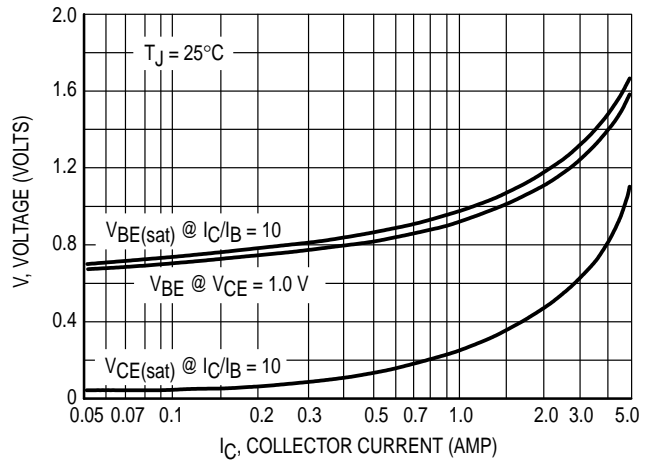
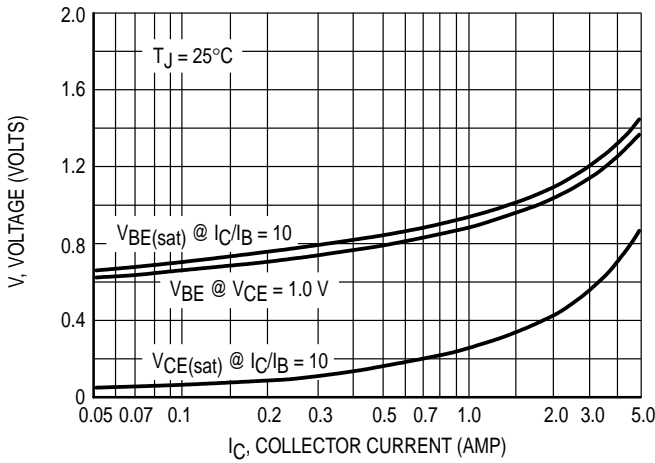


Figure 7. Capacitance

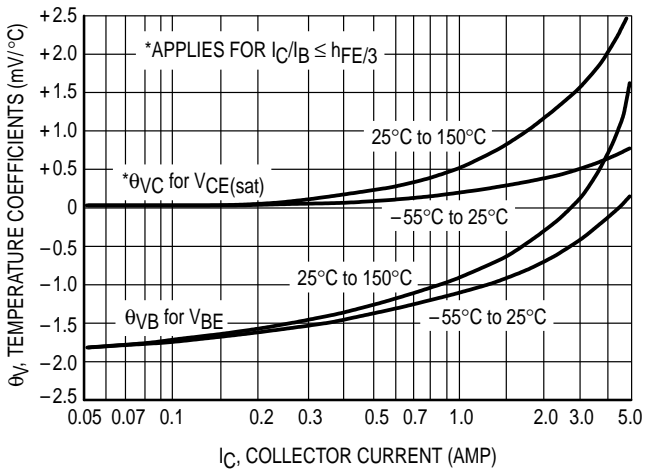
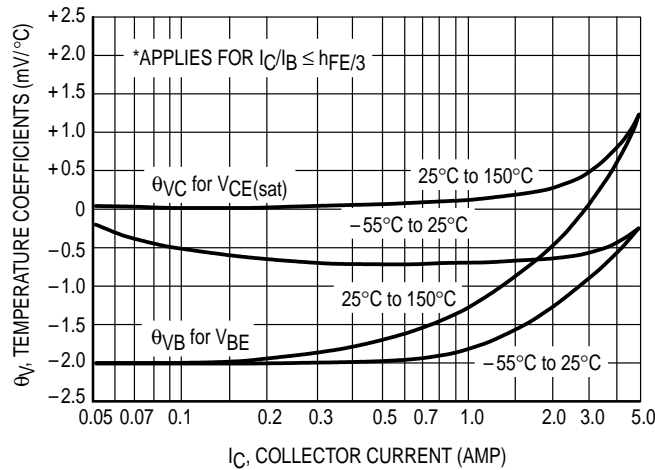
**MJE200 MJE210**



**Figure 8. DC Current Gain**

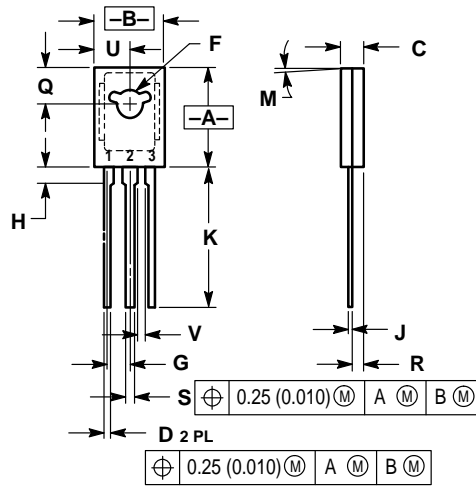


**Figure 9. "On" Voltage**



**Figure 10. Temperature Coefficients**

PACKAGE DIMENSIONS




- NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.055	1.15	1.39
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	—	1.02	—

- STYLE 1:  
 PIN 1. EMITTER  
 2. COLLECTOR  
 3. BASE

CASE 77-08  
 TO-225AA  
 ISSUE V

## MJE200 MJE210

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